

BUK9675-55A

N-channel TrenchMOS logic level FET Rev. 2 — 8 February 2011

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	55	V
I _D	drain current	$V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	20	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	62	W



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}$	-	-	81	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}$	-	58	68	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{Figure 13}};$	-	64	75	mΩ
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 12 A; $V_{sup} \le 55$ V; $R_{GS} = 50 \Omega$; $V_{GS} = 5$ V; $T_{j(init)} = 25 ^{\circ}C$; unclamped	-	-	72	mJ

2. Pinning information

Table 2. Pinning information

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BUK9675-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
			HIGA	Ullit
drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	55	V
drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
gate-source voltage		-10	10	V
drain current	$T_{mb} = 25 \text{ °C}$; $V_{GS} = 5 \text{ V}$; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	20	Α
	T _{mb} = 100 °C; V _{GS} = 5 V; see <u>Figure 1</u>	-	14	Α
peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3	-	81	Α
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	62	W
storage temperature		-55	175	°C
junction temperature		-55	175	°C
peak gate-source voltage	pulsed; t _p ≤ 50 μs	-15	15	V
iode				
source current	T _{mb} = 25 °C	-	20	Α
peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	81	Α
gedness				
non-repetitive drain-source avalanche energy	I_D = 12 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	72	mJ
i	drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature peak gate-source voltage ode source current peak source current ledness non-repetitive drain-source	drain-gate voltage $R_{GS} = 20 \text{ k}\Omega$ gate-source voltage drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \underline{\text{Figure 1}}; \text{ see } \underline{\text{Figure 3}}$ $T_{mb} = 100 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \underline{\text{Figure 1}}$ peak drain current $T_{mb} = 25 \text{ °C}; \text{ pulsed}; t_p \leq 10 \mu \text{s}; \text{ see } \underline{\text{Figure 3}}$ total power dissipation $T_{mb} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 2}}$ storage temperature junction temperature peak gate-source voltage pulsed; $t_p \leq 50 \mu \text{s}$ ode source current $T_{mb} = 25 \text{ °C}$ peak source current pulsed; $t_p \leq 10 \mu \text{s}; T_{mb} = 25 \text{ °C}$ peak source current $T_{mb} = 25 \text{ °C}$ peak source current $T_{mb} = 25 \text{ °C}$ peak source current $T_{mb} = 25 \text{ °C}$	drain-gate voltage $R_{GS} = 20 \text{ k}\Omega$ - gate-source voltage -10 drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 5 \text{V}; \text{see Figure 1}; \text{see Figure 3}$ $T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 5 \text{V}; \text{see Figure 1}$ - peak drain current $T_{mb} = 25 ^{\circ}\text{C}; \text{pulsed}; t_p \leq 10 \mu\text{s}; \text{see Figure 2}$ - storage temperature $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2}$ - storage temperature $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2}$ - 55 peak gate-source voltage pulsed; $t_p \leq 50 \mu\text{s}$ -15 ode source current $T_{mb} = 25 ^{\circ}\text{C}$ - peak source current $T_{mb} = 25 ^{\circ}\text{C}$ - T_{mb	drain-gate voltage $R_{GS} = 20 \text{ k}\Omega$ - 55 gate-source voltage -10 10 10 drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 5 V; \text{see Figure 1}; - 20 \\ \text{see Figure 3} \\ T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 5 V; \text{see Figure 1} - 14 \\ \text{peak drain current} & T_{mb} = 25 ^{\circ}\text{C}; \text{pulsed}; t_p \leq 10 \mu\text{s}; - 81 \\ \text{see Figure 3} & - 62 \\ \text{storage temperature} & -55 & 175 \\ \text{junction temperature} & -55 & 175 \\ \text{peak gate-source voltage} & \text{pulsed}; t_p \leq 50 \mu\text{s} & -15 & 15 \\ \text{ode} & - 20 \\ \text{peak source current} & - 20 \\ \text{peak source current} & - 210 \mu\text{s}; T_{mb} = 25 ^{\circ}\text{C} & - 20 \\ \text{peak source current} & - 120 \mu\text{s}; T_{mb} = 25 ^{\circ}\text{C} & - 81 \\ \text{ledness} & - 72 \\ \text{non-repetitive drain-source} & I_D = 12 \text{A}; V_{\text{sup}} \leq 55 \text{V}; R_{GS} = 50 \Omega; & - 72 \\ \end{array}$

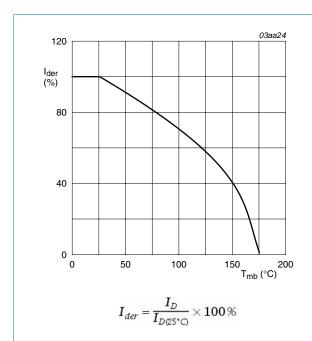


Fig 1. Normalized continuous drain current as a function of mounting base temperature

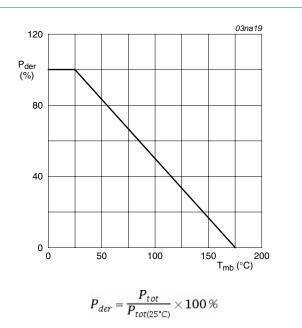
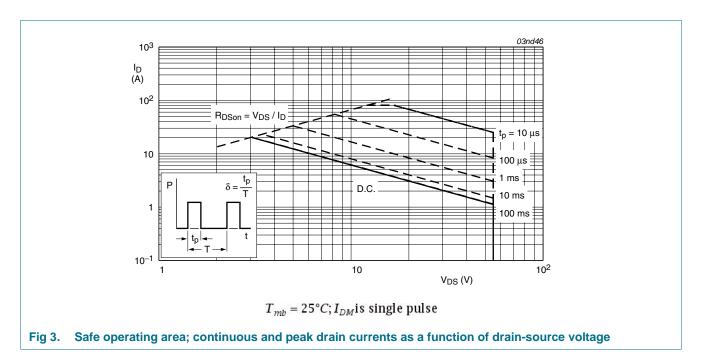


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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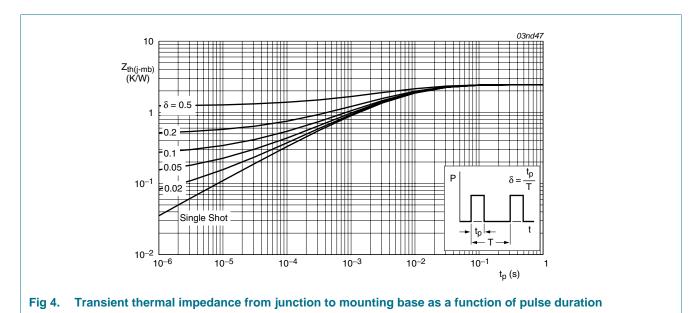
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W



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6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source breakdown voltage		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V	
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 11</u>	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 11</u>	1	1.5	2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 11</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
I _{GSS} gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA	
	$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ	
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}$; $I_D = 10 \text{ A}$; $T_j = 175 \text{ °C}$; see Figure 12; see Figure 13	-	-	150	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}$	-	-	81	$m\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}$	-	58	68	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	64	75	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	440	643	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	90	111	pF
C_{rss}	reverse transfer capacitance		-	60	93	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	47	-	ns
t _{d(off)}	turn-off delay time		-	28	-	ns
t _f	fall time		-	33	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25$ °C	-	2.5	-	nΗ
		from drain lead 6 mm from package to centre of die; $T_j = 25$ °C	-	4.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	33	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	60	-	nC

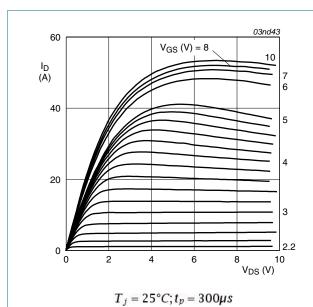


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

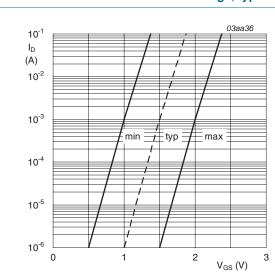


Fig 7. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25 \,{}^{\circ}C; V_{DS} = V_{GS}$

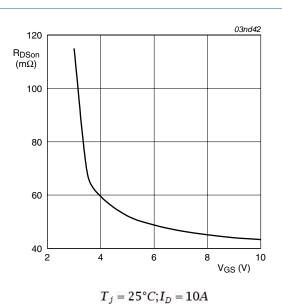


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

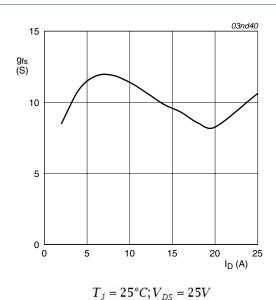
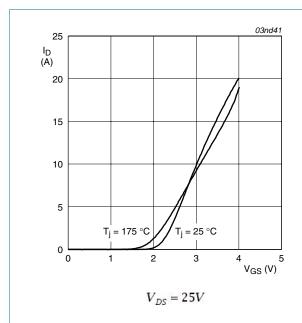
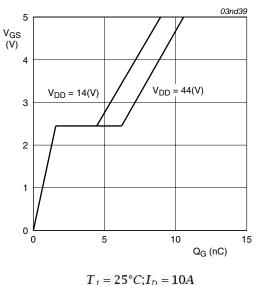


Fig 8. Forward transconductance as a function of drain current; typical values



Transfer characteristics: drain current as a Fig 9. function of gate-source voltage; typical values



 $T_j = 25^{\circ}C; I_D = 10A$

Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values

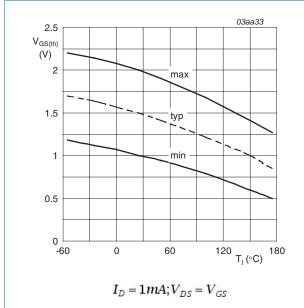


Fig 11. Gate-source threshold voltage as a function of junction temperature

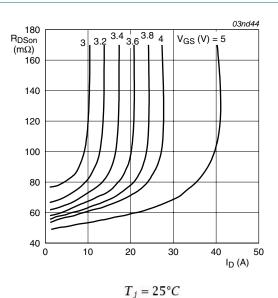


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

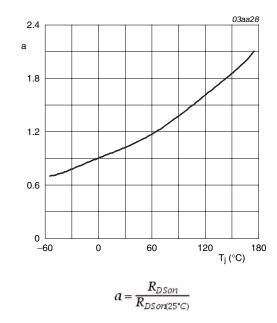
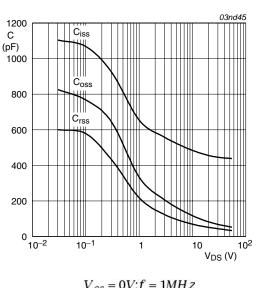


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

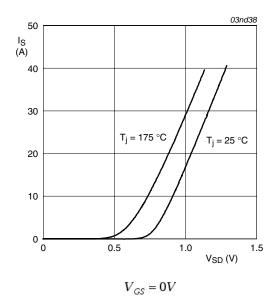


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

7. Package outline

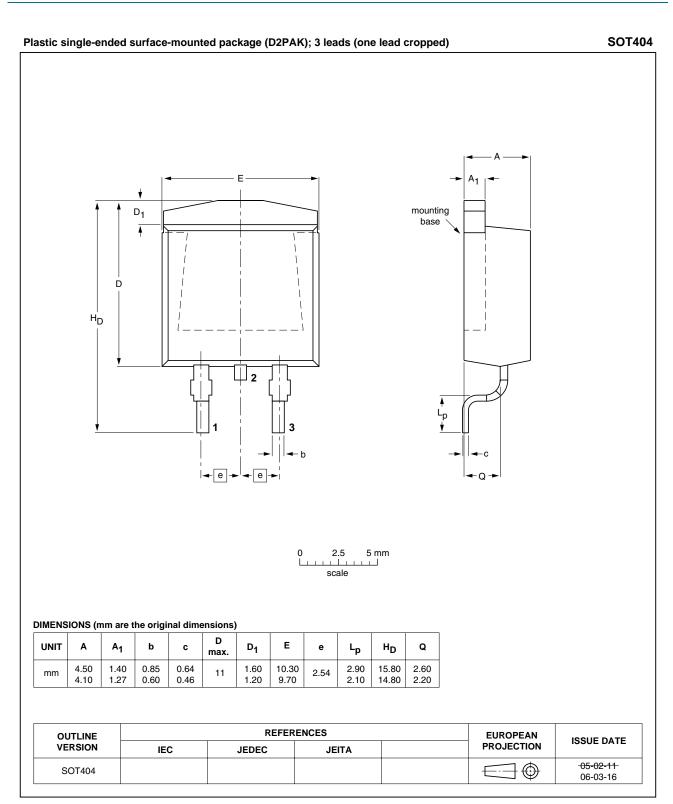


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9675-55A v.2	20110208	Product data sheet	-	BUK9575_9675_55A v.1
Modifications:		of this data sheet has been NXP Semiconductors.	n redesigned to co	mply with the new identity
	 Legal texts h 	ave been adapted to the	new company nam	ne where appropriate.
	 Type numbe 	r BUK9675-55A separate	d from data sheet I	BUK9575_9675_55A v.1.
BUK9575_9675_55A v.1	20010209	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel TrenchMOS logic level FET

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